



PJQA6V2

Transient Voltage Suppressors for ESD Protection

This quad monolithic silicon voltage suppressor is designed for applications requiring transient overvoltage protection capability. It is intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment, and other applications. Its quad junction common anode design protects four separate lines using only one package. These devices are ideal for situations where board space is at a premium.

VOLTAGE 4.3 Volts **POEWR** 150 Watts

SOT23-6L

Unit: inch (mm)

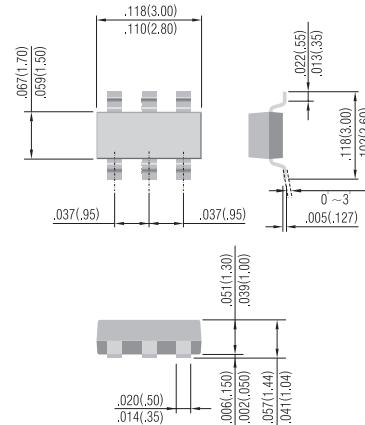
FEATURES

- In compliance with EU RoHS 2002/95/EC directives

MECHANICAL DATA

Case: SOT23-6L Molded plastic

Terminals: Solder plated, solderable per MIL-STD-750, Method 2026



THERMAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Characteristic	Symbol	Value	Unit
Peak Power Dissipation @ 1.0ms @ T A≤25°C	P _{PK}	24	W
Peak Power Dissipation @ 20 μs @ T A≤25°C	P _{PK}	150	W
Total Power Dissipation on FR-4 Board@ T A≤25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance from Junction - to -Ambient	R _{θJA}	556	°C/W
Total Power Dissipation on Alumina Substrate @ T A≤25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance from Junction - to -Ambient	R _{θJA}	417	°C/W
Junction and Storage Temperature Range	T _{J,TSTG}	-55 to + 150	°C
Lead Solder Temperature - Maximum (10 Second Duration)	T _L	260	°C

www.DataSheet4U.com

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Device	Breakdown Voltage				Max Reverse Leakage Current		Max Zener Impedance		Max Reverse Surge Current		Maximum Temperature Coefficient of V _Z
					I _R	V _R	Z _{ZT} @ I _{ZT}		I _{RSRM}	V _{RSRM}	
	Min	Nom	Max	mA	nA	V	Ω	mA	A	V	mV/°C
PJQA6V2	5.89	6.2	6.51	1.0	700	4.3	300		10	9.5	10.6



PJQA6V2

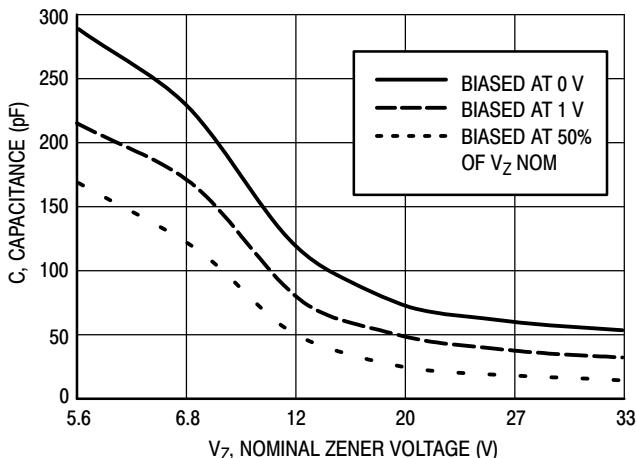


Figure 1. Typical Capacitance

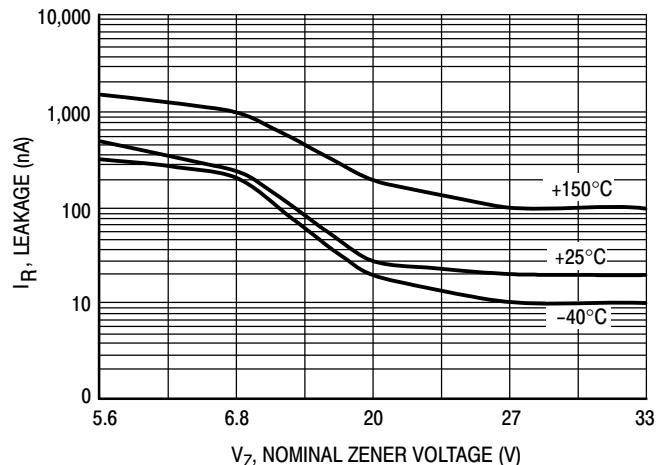


Figure 2. Typical Leakage Current

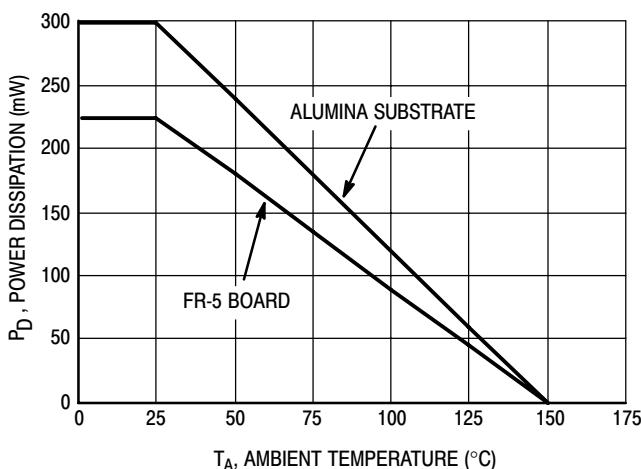


Figure 3. Steady State Power Derating Curve

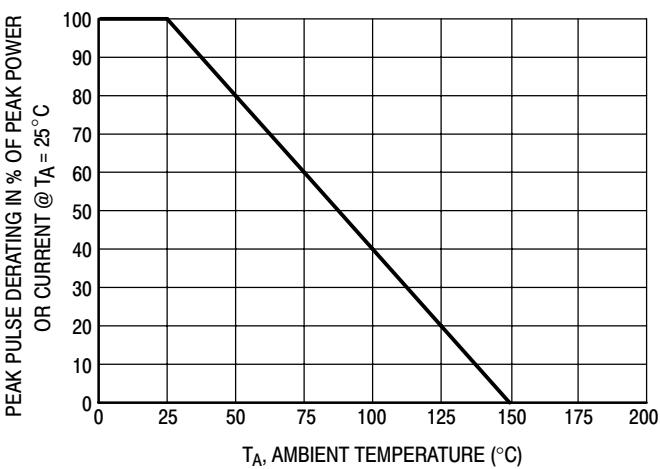


Figure 4. Pulse Derating Curve

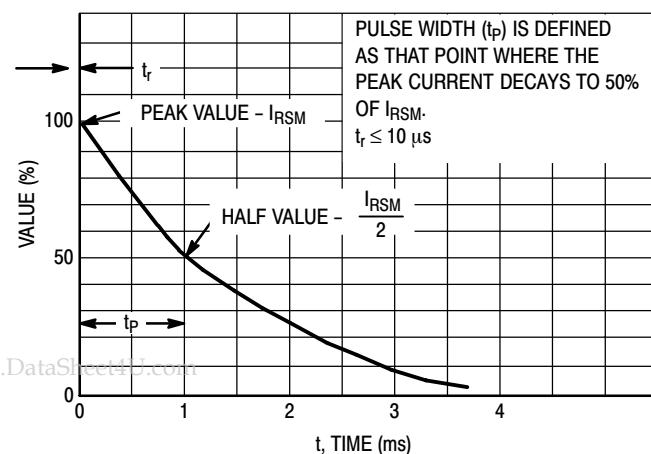


Figure 5. 10 × 1000 μs Pulse Waveform

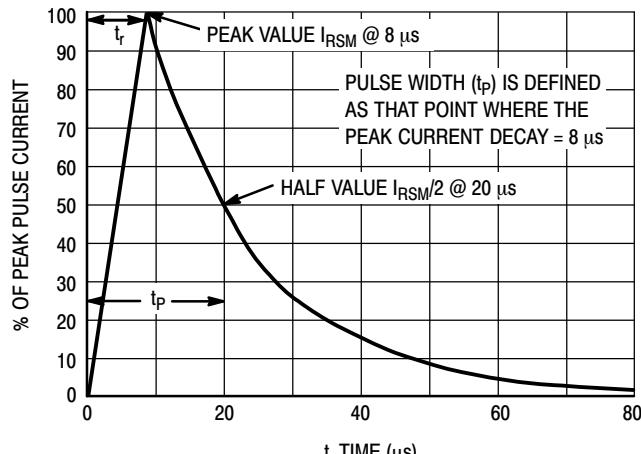


Figure 6. 8 × 20 μs Pulse Waveform



PJQA6V2

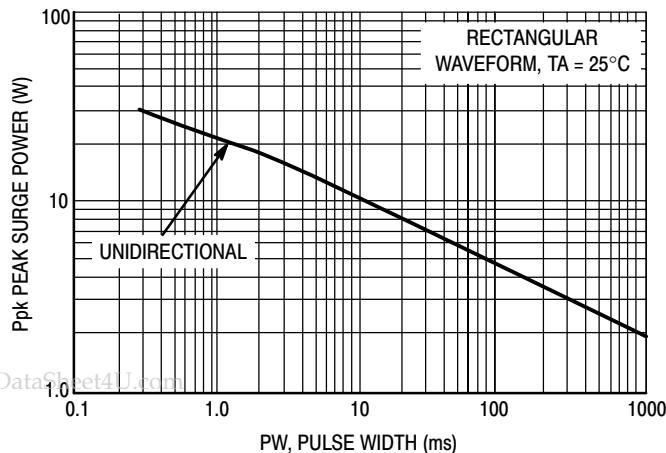


Figure 7. Maximum Non-Repetitive Surge Power, P_{pk} versus PW

Power is defined as $V_{RSM} \times I_Z(pk)$ where V_{RSM} is the clamping voltage at $I_Z(pk)$.

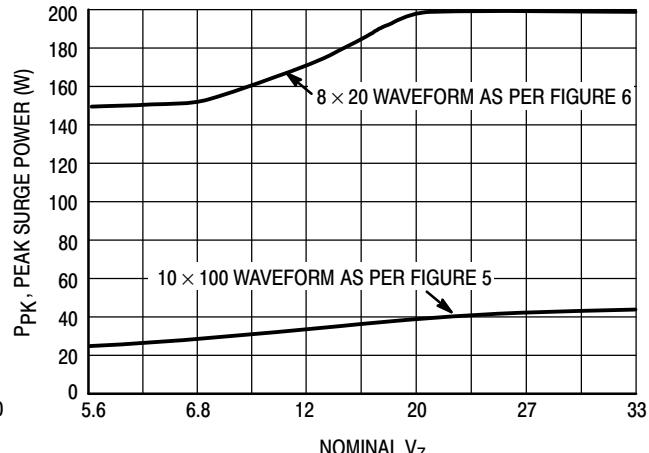
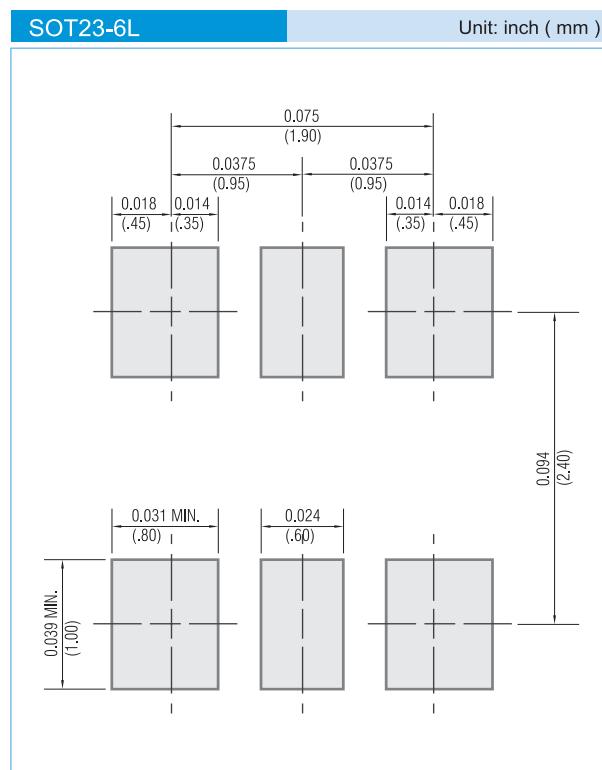


Figure 8. Typical Maximum Non-Repetitive Surge Power, P_{pk} versus V_{BR}



PJQA6V2

MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information
- T/R - 10K per 13" plastic Reel
 T/R - 3K per 7" plastic Reel

LEGAL STATEMENT

Copyright PanJit International, Inc 2009

The information presented in this document is believed to be accurate and reliable. The specifications and information herein are subject to change without notice. Pan Jit makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose. Pan Jit products are not authorized for use in life support devices or systems. Pan Jit does not convey any license under its patent rights or rights of others.